

FLASH MEMORY WITH LOW TUNNEL BARRIER INTERPOLY INSULATORS

Abstract of the Disclosure

5 Structures and methods for Flash memory with low tunnel barrier intergate
insulators are provided. The non-volatile memory includes a first source/drain
region and a second source/drain region separated by a channel region in a substrate.
A floating gate opposing the channel region and is separated therefrom by a gate
oxide. A control gate opposes the floating gate. The control gate is separated from
10 the floating gate by a low tunnel barrier intergate insulator. The low tunnel barrier
intergate insulator includes a metal oxide insulator selected from the group
consisting of PbO, Al₂O₃, Ta₂O₅, TiO₂, ZrO₂, and Nb₂O₅. The floating gate includes
a polysilicon floating gate having a metal layer formed thereon in contact with the
low tunnel barrier intergate insulator. And, the control gate includes a polysilicon
15 control gate having a metal layer formed thereon in contact with the low tunnel
barrier intergate insulator.

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